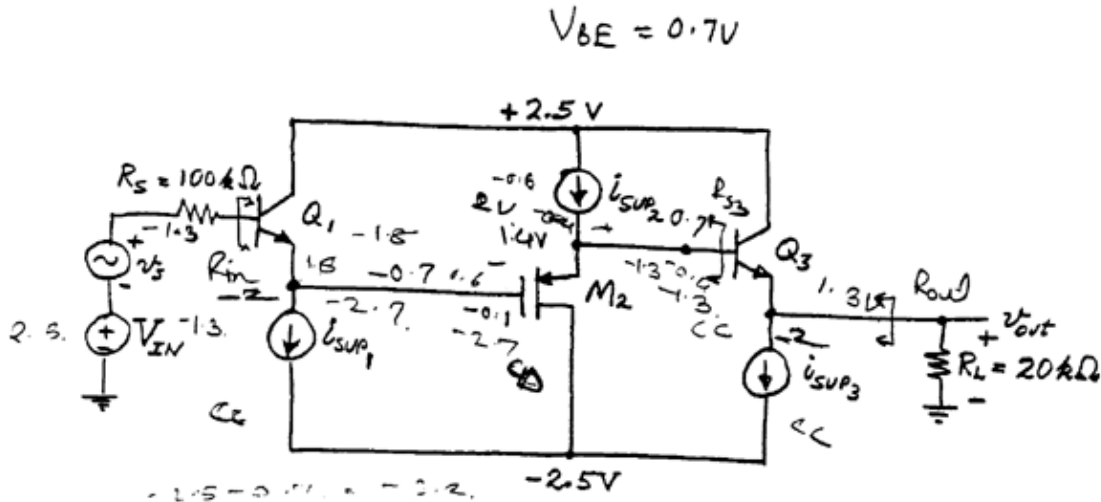


Ground Rules:

- Close book; one 8.5x11 crib sheet (both sides)
- Do all work on exam pages
- Default bipolar transistor parameters:
 - ◆ npn: $\beta_n=100$, $V_{An}=50$ V, $V_{CE-sat}=0.2$ V
 - ◆ pnp: $\beta_p=50$, $V_{Ap}=25$ V, $V_{EC-sat}=0.2$ V
- Default MOS transistor parameters: note LAMBDA depends on L!
 - ◆ NMOS: $\mu_n C_{ox}=100e-6$ A/V², $LAMBDA_n=[0.1/L]$ V⁻¹ (L in micrometers) $V_{Tp}=1$ V
 - ◆ PMOS: $\mu_p C_{ox}=50e-6$ A/V², $LAMBDA_p=[0.1/L]$ V⁻¹ (L in micrometers) $V_{Tp}=-1$ V

Problem #1: Small-Signal Amplifier [24 points]



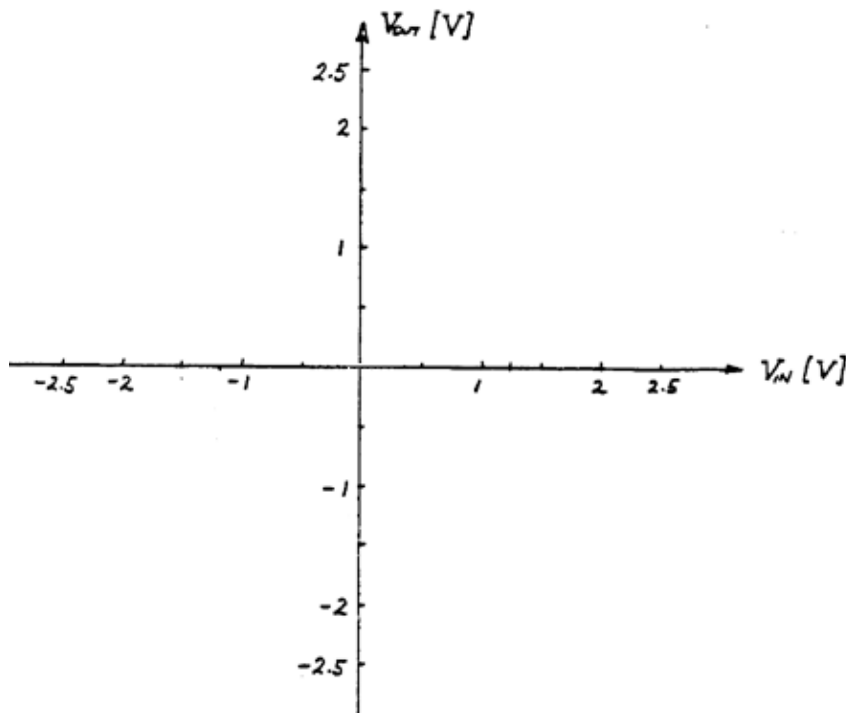
GIVEN: $I_{SUP1} = 100\mu A$ $r_{OC1} = 200k\Omega$ $V_{SUP(min)} = 0.5V$
 $I_{SUP2} = 200\mu A$ $r_{OC2} = 100k\Omega$
 $I_{SUP3} = 100\mu A$ $r_{OC3} = 200k\Omega$

- a) [4 pts.] What is width of transistor M_2 such that the DC output voltage $V_{out}=0$ V for $V_{IN}=0$ V. Given: the length of M_2 is $L_2=2e-6$ m.
- b) [4 pts.] What is the numerical value of the input resistance R_{in} of this amplifier? Your answer should be correct to within +/- 5%.
- If you couldn't solve (a) you can assume for this part that $W_2=25e-6$ m. Of course, this isn't the correct answer to part (a).

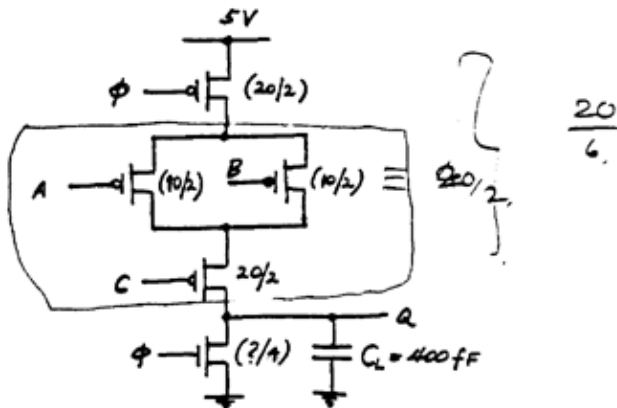
c) [4 pts.] What is the numerical value of the output resistance R_{out} of this amplifier? Your answer should be correct to within $\pm 5\%$.
 If you couldn't solve (a) you can assume for this part that $W_2=25e-6$ m. Of course, this isn't the correct answer to part (a).

d) [6 pts.] What is the numerical value of the overall voltage gain v_{out}/v_s , with $R_s=100$ kilo-ohms and $R_L=20$ kilo-ohms? Your answer should be correct to within $\pm 5\%$.
 Again, If you couldn't solve (a) you can assume for this part that $W_2=25e-6$ m. Of course, this isn't the correct answer to part (a).

e) [6 pts.] Sketch the transfer curve V_{OUT} versus V_{IN} for $-2.5 \leq V_{IN} \leq +2.5$ V on the graph below. For this part, R_L is infinity and $R_S=0$ V.
 Hint: you should note that the current supplies each require at least $V_{SUP(min)}=0.5$ V in order to function.

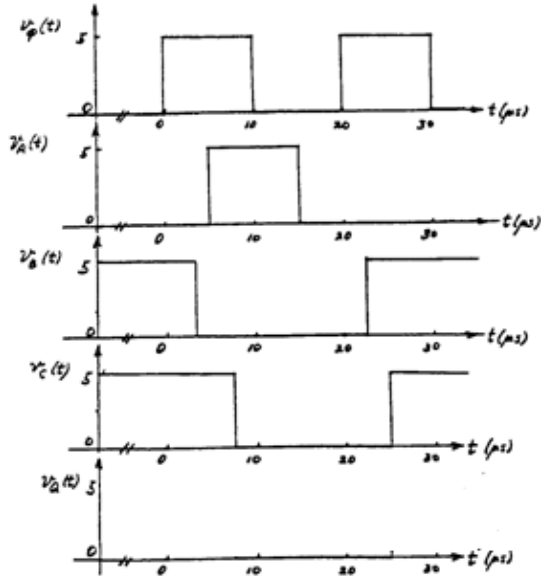


Problem #2: Digital Logic Gate [14 points]



a) [2 pts.] What is the logic operation performed by the above circuit? In other words, what is the logical expression for Q in terms of the three inputs A, B and C?

b) [4 pts.] The graphs below plot the voltage waveforms over an interval of 35 microseconds. Fill in the output voltage waveform $v_Q(t)$ over $0 \rightarrow 35 \mu\text{s}$. Note that the rise and fall times are essentially zero on this time scale.

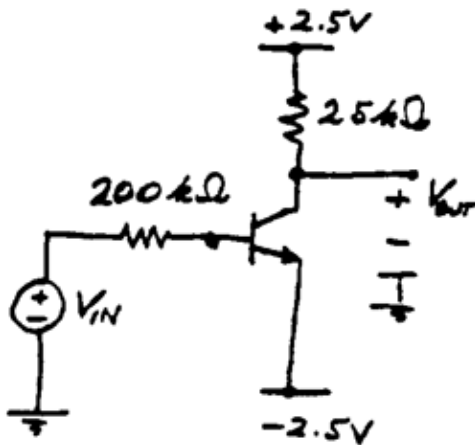


c) [4 pts.] Find the numerical value of the **best case** low-to-high propagation delay (t_{PLH}) for this logic gate.

d) [4 pts.] Find the width of the n-channel transistor such that the high-to-low propagation delay (t_{PLH}) is equal to your answer for part c). If you couldn't answer part c) you can assume for this part that $t_{PLH}(\text{best}) = 1 \text{ ns} = 10^{-9}\text{s}$.

Problem #3: Bipolar Transistor Physics [12 points]

NOTE: The default npn transistors do not apply for this problem!



GIVEN:

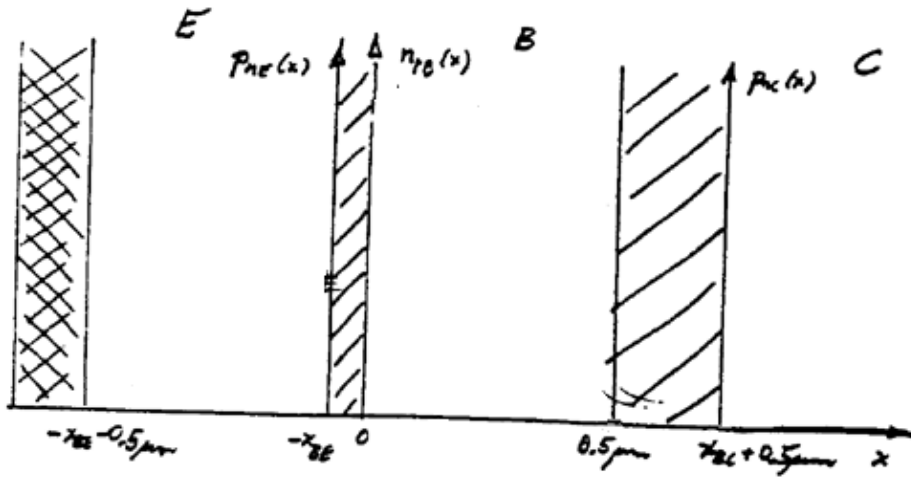
$$N_{dE} = 2 \times 10^{18} \text{ cm}^{-3}$$

$$N_{dB} = 10^{17} \text{ cm}^{-3}$$

$N_{dC}=10^{16} \text{ cm}^{-3}$

The base and emitter widths are $W_B=W_E=0.5 \text{ micrometers}$. The electron diffusion coefficient in the base is $D_{nB}=10 \text{ cm}^2/\text{s}$ and the hole diffusion coefficient in the emitter is $D_{pE}=5 \text{ cm}^2/\text{s}$.

a) [3 pts.] Qualitatively sketch the minority carrier concentrations in the emitter, base and collector on the graph below, assuming that the transistor is biased in the forward active region.



b) [3 pts.] For $V_{OUT}=0 \text{ V}$ what is the numerical value of the minority electron concentration at $x=0$, $n_{pB}(0)$? You can assume that the transistor is biased in the forward active region.

c) [3 pts.] What is the numerical value of the base current I_B for the bias condition in part b)? If you couldn't solve b) assume for this part that $n_{pB}(0) = 10^{15} \text{ cm}^{-3}$ -- not the correct answer to b), of course. d) [3 pts.] What is the numerical value of V_{IN} in order that the transistor is biased in the forward active region with $V_{OUT}=0 \text{ V}$?

Notes: You cannot assume that $V_{BE}=0.7 \text{ V}$ for this part. If you couldn't solve parts b) and c) you can assume that $n_{pB}(0)=10^{15} \text{ cm}^{-3}$ and that $I_B=4 \text{ micro-amps}$. Neither of these answers are correct, of course.

Answers!

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